

CD4518BMS, CD4520BMS

December 1992

CMOS Dual Up Counters

Features

- High Voltage Types (20V Rating)
- CD4518BMS Dual BCD Up Counter
- CD4520BMS Dual Binary Up Counter
- Medium Speed Operation
 - 6MHz Typical Clock Frequency at 10V
- · Positive or Negative Edge Triggering
- Synchronous Internal Carry Propagation
- 100% Tested for Quiescent Current at 20V
- 5V, 10V and 15V Parametric Ratings
- Maximum Input Current of 1μA at 18V Over Full Package Temperature Range; 100nA at 18V and +25°C
- Noise Margin (Over Full Package/Temperature Range)
 - 1V at VDD = 5V
 - 2V at VDD = 10V
 - 2.5V at VDD = 15V
- Standardized Symmetrical Output Characteristics
- Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications

- Multistage Synchronous Counting
- Multistage Ripple Counting
- Frequency Dividers

Description

CD4518BMS Dual BCD Up Counter and CD4520BMS Dual Binary Up Counter each consist of two identical, internally synchronous 4-stage counters. The counter stages are D-type flip-flops having interchangeable CLOCK and ENABLE lines for incrementing on either the positive-going or negative-going transition. For single unit operation the ENABLE input is maintained high and the counter advances on each positive-going transition of the CLOCK. The counters are cleared by high levels on their RESET lines.

The counter can be cascaded in the ripple mode by connecting Q4 to the enable input of the subsequent counter while the CLOCK input of the latter is held low.

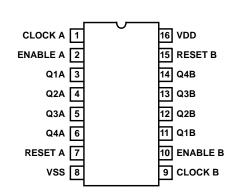
The CD4518BMS and CD4520BMS are supplied in these 16-lead outline packages:

Braze Seal DIP H4S Frit Seal DIP H1F

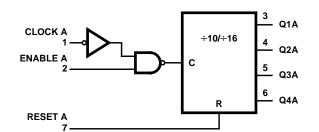
Ceramic Flatpack *H6P †H6W *CD4518B Only †CD4520B Only

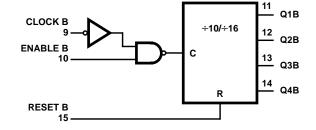
Pinout

CD4518BMS, CD4520BMS TOP VIEW



Functional Diagram





VSS = 8 VDD = 16

Absolute Maximum Ratings

DC Supply Voltage Range, (VDD) -0.5V to +20V (Voltage Referenced to VSS Terminals) Input Voltage Range, All Inputs -0.5V to VDD +0.5V DC Input Current, Any One Input±10mA Operating Temperature Range -55°C to +125°C Package Types D, F, K, H Storage Temperature Range (TSTG) -65°C to +150°C Lead Temperature (During Soldering) +265°C At Distance 1/16 \pm 1/32 Inch (1.59mm \pm 0.79mm) from case for 10s Maximum

Reliability Information

Thermal Resistance	θ_{ja}	θ _{jc} 20°C/W
Ceramic DIP and FRIT Package	80°C/W	20°C/W
Flatpack Package	70°C/W	20°C/W
Maximum Package Power Dissipation (PD	o) at +125°C	
For T _A = -55°C to +100°C (Package Typ		
For $T_A = +100^{\circ}$ C to $+125^{\circ}$ C (Package T	ype D, F, K).	Derate
Lineari	ity at 12mW/	°C to 200mW
Device Dissipation per Output Transistor .		100mW
For T _A = Full Package Temperature Rar	nge (All Pack	age Types)
Junction Temperature		+175°C

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

				GROUP A		LIMITS			
PARAMETER	SYMBOL	CONDITIONS (NOTE 1)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS	
Supply Current	IDD	VDD = 20V, VIN = VD	D or GND	1	+25°C	-	10	μΑ	
				2	+125°C	-	1000	μА	
		VDD = 18V, VIN = VD	D or GND	3	-55°C	-	10	μА	
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA	
				2	+125°C	-1000	-	nA	
			VDD = 18V	3	-55°C	-100	-	nA	
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA	
				2	+125°C	-	1000	nA	
			VDD = 18V	3	-55°C	-	100	nA	
Output Voltage	VOL15	VDD = 15V, No Load	·	1, 2, 3	+25°C, +125°C, -55°C	-	50	mV	
Output Voltage	VOH15	VDD = 15V, No Load	(Note 3)	1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V	
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.	.4V	1	+25°C	0.53	-	mA	
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0	0.5V	1	+25°C	1.4	-	mA	
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1	VDD = 15V, VOUT = 1.5V		+25°C	3.5	-	mA	
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-0.53	mA	
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.	.5V	1	+25°C	-	-1.8	mA	
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9	9.5V	1	+25°C	-	-1.4	mA	
Output Current (Source)	IOH15	VDD = 15V, VOUT = 1	13.5V	1	+25°C	-	-3.5	mA	
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10)μΑ	1	+25°C	-2.8	-0.7	V	
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10μ/	A	1	+25°C	0.7	2.8	٧	
Functional	F	VDD = 2.8V, VIN = V	DD or GND	7	+25°C	VOH>	VOL <	V	
		VDD = 20V, VIN = VD	D or GND	7	+25°C	VDD/2	VDD/2		
		VDD = 18V, VIN = VD	D or GND	8A	+125°C				
		VDD = 3V, VIN = VDD	or GND	8B	-55°C				
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V	
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V	
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13 VOL < 1.5V	3.5V,	1, 2, 3	+25°C, +125°C, -55°C	-	4	V	
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13 VOL < 1.5V	3.5V,	1, 2, 3	+25°C, +125°C, -55°C	11	-	V	

NOTES: 1. All voltages referenced to device GND, 100% testing being 3. For accuracy, voltage is measured differentially to VDD. Limit implemented.

is 0.050V max.

2. Go/No Go test with limits applied to inputs.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

			GROUP A		LIM	ITS	
PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Propagation Delay	TPHL1	VDD = 5V, VIN = VDD or GND	9	+25°C	-	560	ns
Clock to Output	TPLH1		10, 11	+125°C, -55°C	-	756	ns
Propagation Delay TPHI		VDD = 5V, VIN = VDD or GND	9	+25°C	-	650	ns
Reset to Ouput			10, 11	+125°C, -55°C	-	878	ns
Transition Time	TTHL VDD = 5V, VIN = VDD or		9	+25°C	-	200	ns
(Note 2)	TTLH		10, 11	+125°C, -55°C	-	270	ns
Maximum Clock Input	FCL	VDD = 5V, VIN = VDD or GND	9	+25°C	1.5	-	MHz
Frequency			10, 11	+125°C, -55°C	1.11	-	MHz

NOTES:

- 1. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
- 2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIN	IITS		
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS	
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	5	μΑ	
				+125°C	-	150	μΑ	
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	μΑ	
				+125°C	-	300	μΑ	
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	μΑ	
				+125°C	-	600	μΑ	
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV	
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV	
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	٧	
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V	
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA	
				-55°C	0.64	-	mA	
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA	
				-55°C	1.6	-	mA	
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA	
				-55°C	4.2	-	mA	
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA	
				-55°C	-	-0.64	mA	
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA	
				-55°C	-	-2.0	mA	
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA	
				-55°C	-	-1.6	mA	
Output Current (Source)	IOH15	VDD =15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA	
				-55°C	-	-4.2	mA	
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V	
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	+7	-	V	

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

					LIMITS		
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Propagation Delay	TPHL1	VDD = 10V	1, 2, 3	+25°C	-	230	ns
Clock to Output	TPLH1	VDD = 15V	1, 2, 3	+25°C	-	160	ns
Propagation Delay	TPHL2	VDD = 10V	1, 2, 3	+25°C	-	225	ns
Reset to Output		VDD = 15V	1, 2, 3	+25°C	-	170	ns
Transition Time	TTHL	VDD = 10V	1, 2, 3	+25°C	-	100	ns
	TTLH	VDD = 15V	1, 2, 3	+25°C	-	80	ns
Maximum Clock Input	FCL	VDD = 10V	1, 2, 3	+25°C	3	-	MHz
Frequency		VDD = 15V	1, 2, 3	+25°C	4	-	MHz
Maximum Clock Rise and	TRCL TFCL	VDD = 5V	1, 2, 3, 4	+25°C	-	15	μs
Fall Time		VDD = 10V	1, 2, 3, 4	+25°C	-	5	μs
		VDD = 15V	1, 2, 3, 4	+25°C	-	5	μs
Minimum Enable Pulse	TW	VDD = 5V	1, 2, 3	+25°C	-	400	ns
Width		VDD = 10V	1, 2, 3	+25°C	-	200	ns
		VDD = 15V	1, 2, 3	+25°C	-	140	ns
Minimum Reset Pulse	TW	VDD = 5V	1, 2, 3	+25°C	-	250	ns
Width		VDD = 10V	1, 2, 3	+25°C	-	110	ns
		VDD = 15V	1, 2, 3	+25°C	-	80	ns
Minimum Clock Pulse	TW	VDD = 5V	1, 2, 3	+25°C	-	200	ns
Width		VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	70	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	7.5	pF

NOTES:

- 1. All voltages referenced to device GND.
- 2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
- 3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
- 4. If more than one unit is cascaded, TRCL should be made less than or equal to the sumof the transition time and the fixed propagation delay of the output of the driving stage for the estimated capacitive load.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

			LIM				
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	25	μΑ
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10μA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH >	VOL <	V
		VDD = 3V, VIN = VDD or GND			VDD/2	VDD/2	
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.

3. See Table 2 for $+25^{\circ}$ C limit.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-2	IDD	± 1.0μA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (F	re Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test	1 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test	2 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note	: 1)	100% 5004	1, 7, 9, Deltas	
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1.5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

	MIL-STD-883	TEST		READ AND	RECORD
CONFORMANCE GROUPS	METHOD	PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

					OSCIL	LATOR
FUNCTION	OPEN	GROUND	VDD	9V ± -0.5V	50kHz	25kHz
Static Burn-In 1 Note 1	3-6, 11-14	1, 2, 7-10, 15	16			
Static Burn-In 2 Note 1	3-6, 11-14	8	1, 2, 7, 9, 10, 15, 16			
Dynamic Burn- In Note 1	-	7, 8, 15	2, 10, 16	3-6, 11-14	1, 9	
Irradiation Note 2	3-6, 11-14	8	1, 2, 7, 9, 10, 15, 16			

NOTES:

- 1. Each pin except VDD and GND will have a series resistor of 10K \pm 5%, VDD = 18V \pm 0.5V
- 2. Each pin except VDD and GND will have a series resistor of 47K \pm 5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = $10V \pm 0.5V$

Logic Diagrams

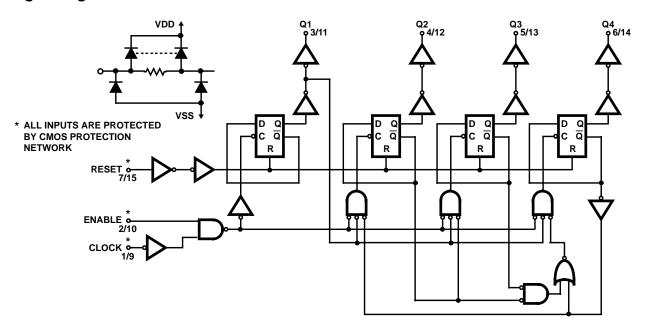


FIGURE 1. DECADE COUNTER (CD4518BMS) LOGIC DIAGRAM FOR ONE OF TWO IDENTICAL COUNTERS

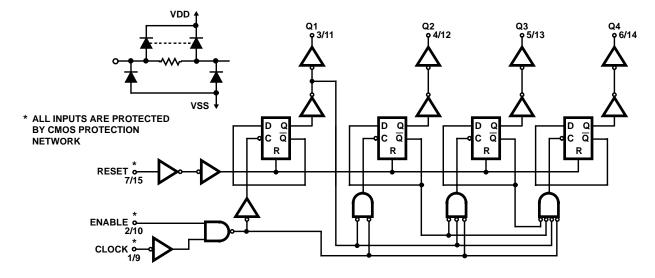


FIGURE 2. BINARY COUNTER (CD4520BMS) LOGIC DIAGRAM FOR ONE OF TWO IDENTICAL COUNTERS

TRUTH TABLE

CLOCK	ENABLE	RESET	ACTION
	1	0	Increment Counter
0	_	0	Increment Counter
	Х	0	No Change
Х		0	No Change
	0	0	No Change
1	/	0	No Change
Х	X	1	Q1 thru Q4 = 0

X = Don't Care 1 = High State 0 = Low State

Typical Performance Curves

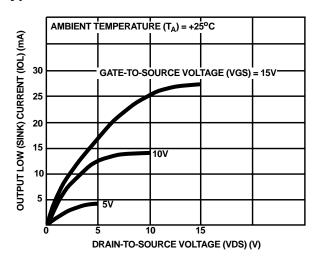


FIGURE 3. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

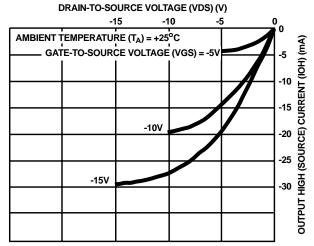


FIGURE 5. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

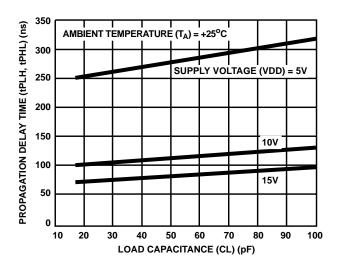


FIGURE 7. TYPICAL PROPAGATION DELAY VS LOAD CAPACITANCE, CLOCK OR ENABLE TO OUTPUT

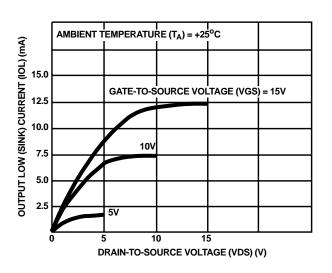


FIGURE 4. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

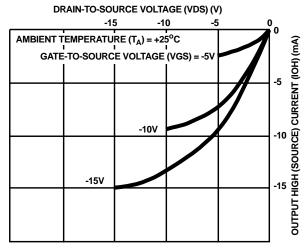


FIGURE 6. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

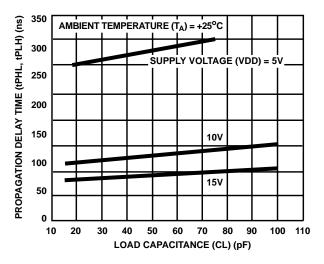
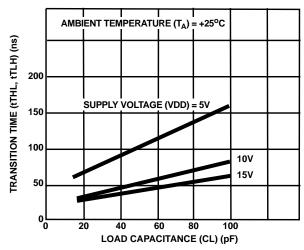


FIGURE 8. TYPICAL PROPAGATION DELAY TIME vs LOAD CAPACITANCE, RESET TO OUTPUT

Typical Performance Curves



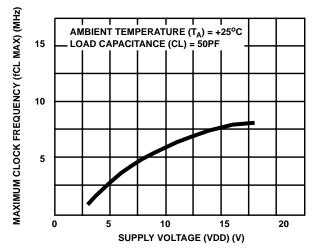


FIGURE 9. TYPICAL TRANSITION TIME vs LOAD CAPACITANCE

FIGURE 10. TYPICAL MAXIMUM CLOCK FREQUENCY vs SUPPLY VOLTAGE

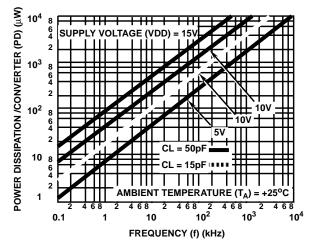


FIGURE 11. TYPICAL POWER DISSIPATION CHARACTERISTICS

Timing Diagrams

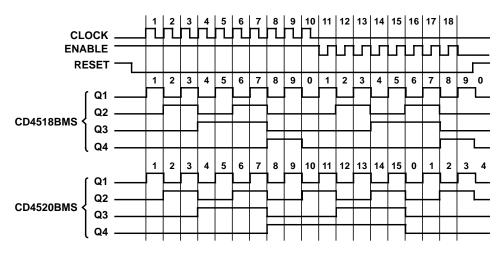


FIGURE 12. TIMING DIAGRAMS FOR CD4518BMS AND CD4520BMS

CD4518BMS, CD4520BMS

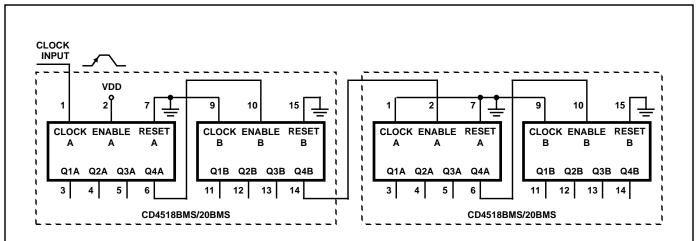
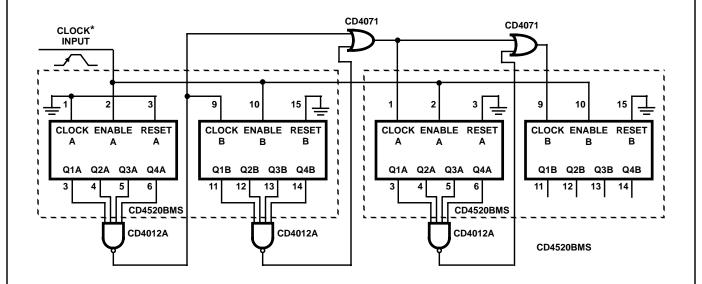


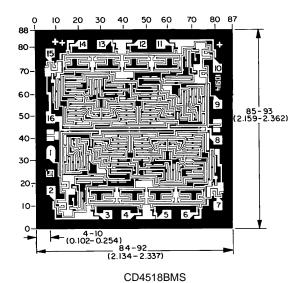
FIGURE 13. RIPPLE CASCADING OF FOUR COUNTERS WITH POSITIVE EDGE TRIGGERING

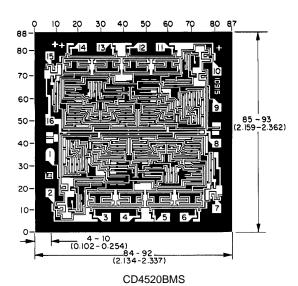


^{*} For synchronous cascading, the clock transition time should be made less than or equal to the sum of the fixed propagation delay at 15pF and the transition time of the output driver stage for the estimated capacitive load.

FIGURE 14. SYNCHRONOUS CASCADING OF FOUR BINARY COUNTERS WITH NEGATIVE EDGE TRIGGERING

Chip Dimensions and Pad Layouts





Dimensions in parenthesis are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10-3 inch).

METALLIZATION: Thickness: 11kÅ - 14kÅ, AL.

PASSIVATION: 10.4kÅ - 15.6kÅ, Silane

BOND PADS: 0.004 inches X 0.004 inches MIN **DIE THICKNESS:** 0.0198 inches - 0.0218 inches

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